

Enhanced Product

OP284-EP

FEATURES

- Single-supply operation
- Wide bandwidth: 4.25 MHz
- Low offset voltage: 100 μ V
- Unity-gain stable
- High slew rate: 4.0 V/ μ s
- Low noise: 3.9 nV/ $\sqrt{\text{Hz}}$

ENHANCED PRODUCT FEATURES

- Supports defense and aerospace applications (AQEC standard)
- Military temperature range (-55°C to +125°C)
- Controlled manufacturing baseline
- 1 assembly/test site
- 1 fabrication site
- Enhanced product change notification
- Qualification data available on request

APPLICATIONS

- Battery-powered instrumentation
- Power supply control and protection
- Telecommunications
- DAC output amplifier
- ADC input buffer

GENERAL DESCRIPTION

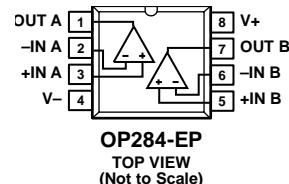
The OP284-EP is a dual, single-supply, 4.25 MHz bandwidth amplifier featuring rail-to-rail inputs and outputs (RRIO).

The OP284-EP is guaranteed to operate from 5 V to 36 V (or ± 2.5 V to ± 18 V).

This amplifier is superb for single-supply applications requiring both ac and precision dc performance. The combination of wide bandwidth, low noise, and precision makes the OP284-EP useful in a wide variety of applications, including filters and instrumentation.

Other applications for this amplifier include portable telecommunications equipment, power supply control and protection,

PIN CONNECTION DIAGRAM



12562-001

Figure 1.

and use as an amplifier or buffer for transducers with wide output ranges. Sensors requiring a rail-to-rail input amplifier include Hall effect, piezoelectric, and resistive transducers.

The ability to swing rail to rail at both the input and output enables designers to build multistage filters in single-supply systems and to maintain high signal-to-noise ratios.

The OP284-EP is specified over the extended industrial temperature range of -55°C to +125°C. The OP284-EP is available in a SOIC surface-mount package.

Rev. 0

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REVISION HISTORY

5/15—Revision 0: Initial Version

SPECIFICATIONS**ELECTRICAL CHARACTERISTICS**

$V_S = 5.0 \text{ V}$, $V_{CM} = 2.5 \text{ V}$, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 1.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		125	250	μV
Input Bias Current	I_B	$-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	60	450	600	nA
Input Offset Current	I_{OS}	$-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		50	5	nA
Input Voltage Range			0	5		V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = 1.0 \text{ V to } 4.0 \text{ V}$, $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	86			dB
Large Signal Voltage Gain	A_{VO}	$R_L = 2 \text{ k}\Omega$, $1 \text{ V} \leq V_{OUT} \leq 4 \text{ V}$	50	240		V/mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$R_L = 2 \text{ k}\Omega$, $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	25	0.2	2.00	$\mu\text{V}/^\circ\text{C}$
Bias Current Drift	$\Delta I_B/\Delta T$			150		$\text{pA}/^\circ\text{C}$
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$I_L = 1.0 \text{ mA}$	4.80			V
Output Voltage Low	V_{OL}	$I_L = 1.0 \text{ mA}$		125		mV
Output Current	I_{OUT}		± 6.5			mA
POWER SUPPLY						
Supply Current/Amplifier	I_{SY}	$V_{OUT} = 2.5 \text{ V}$, $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		1.45		mA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 2 \text{ k}\Omega$	1.65	2.4		$\text{V}/\mu\text{s}$
Settling Time	t_s	To 0.01%, 1.0 V step		2.5		μs
Gain Bandwidth Product	GBP			3.25		MHz
Phase Margin	Φ_M			45		Degrees
NOISE PERFORMANCE						
Voltage Noise	$e_n \text{ p-p}$	0.1 Hz to 10 Hz	0.3			$\mu\text{V p-p}$
Voltage Noise Density	e_n	$f = 1 \text{ kHz}$		3.9		$\text{nV}/\sqrt{\text{Hz}}$
Current Noise Density	i_n			0.4		$\text{pA}/\sqrt{\text{Hz}}$

$V_S = \pm 15.0$ V, $V_{CM} = 0$ V, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 2.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		100	200	μV
Input Bias Current	I_B	$-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	80	450	600	nA
Input Offset Current	I_{OS}	$-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		50	50	nA
Input Voltage Range			-15	+15		V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = -14.0$ V to $+14.0$ V, $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	86	90		dB
Large Signal Voltage Gain	A_{VO}	$R_L = 2 \text{ k}\Omega$, -10 V $\leq V_{OUT} \leq 10$ V	150	1000		V/mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$R_L = 2 \text{ k}\Omega$, $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.2	2.00	$\mu\text{V}/^\circ\text{C}$
Bias Current Drift	$\Delta V_B/\Delta T$			150		$\text{pA}/^\circ\text{C}$
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$I_L = 1.0$ mA	14.8			V
Output Voltage Low	V_{OL}	$I_L = 1.0$ mA		-14.875		V
Output Current	I_{OUT}		± 10			mA
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_S = \pm 2.0$ V to ± 18 V, $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	90			dB
Supply Current/Amplifier	I_{SY}	$V_{OUT} = 0$ V, $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		2.0		mA
		$V_S = \pm 18$ V, $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		2.25		mA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 2 \text{ k}\Omega$	2.4	4.0		$\text{V}/\mu\text{s}$
Full Power Bandwidth	BW_p	1% distortion, $R_L = 2 \text{ k}\Omega$, $V_{OUT} = 29$ V p-p		35		kHz
Settling Time	t_s	To 0.01%, 10 V step		4		μs
Gain Bandwidth Product	GBP			4.25		MHz
Phase Margin	Φ_M			50		Degrees
NOISE PERFORMANCE						
Voltage Noise	e_n p-p	0.1 Hz to 10 Hz	0.3			μV p-p
Voltage Noise Density	e_n	$f = 1$ kHz		3.9		$\text{nV}/\sqrt{\text{Hz}}$
Current Noise Density	i_n			0.4		$\text{pA}/\sqrt{\text{Hz}}$

ABSOLUTE MAXIMUM RATINGS

Table 3.

Parameter	Rating
Supply Voltage	$\pm 18\text{ V}$
Input Voltage	$\pm 18\text{ V}$
Differential Input Voltage ¹	$\pm 0.6\text{ V}$
Output Short-Circuit Duration to GND	Indefinite
Storage Temperature Range	-65°C to $+150^\circ\text{C}$
Operating Temperature Range	-55°C to $+125^\circ\text{C}$
Junction Temperature Range	-65°C to $+150^\circ\text{C}$
Lead Temperature (Soldering 60 sec)	300°C

¹ For input voltages greater than 0.6 V, the input current must be limited to less than 5 mA to prevent degradation or destruction of the input devices.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

THERMAL RESISTANCE

θ_{JA} is specified for the worst-case conditions; that is, θ_{JA} is specified for a device soldered in the circuit board for the SOIC package.

Table 4. Thermal Resistance

Package Type	θ_{JA}	θ_{JC}	Unit
8-Lead SOIC	158	43	°C/W

ESD CAUTION



ESD (electrostatic discharge) sensitive device.

Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

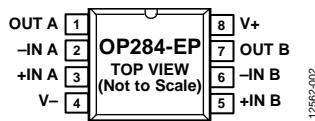


Figure 2. Pin Configuration

Table 5. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	OUT A	Output Channel A.
2	-IN A	Inverting Input Channel A.
3	+INA	Noninverting Input Channel A.
4	V-	Negative Supply Voltage.
5	+IN B	Noninverting Input Channel B.
6	-IN B	Inverting Input Channel B.
7	OUT B	Output Channel B.
8	V+	Positive Supply Voltage.

TYPICAL PERFORMANCE CHARACTERISTICS

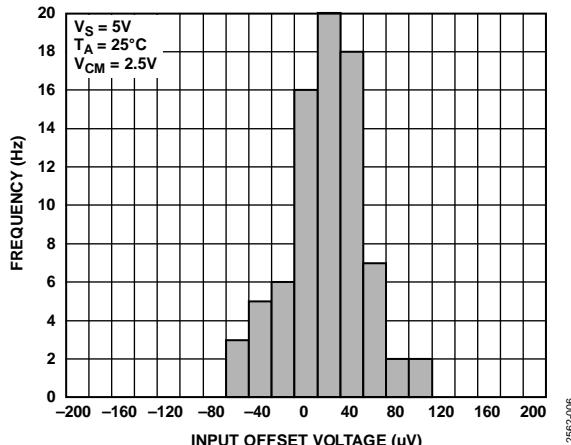


Figure 3. Input Offset Voltage Distribution, $V_S = 5\text{ V}$

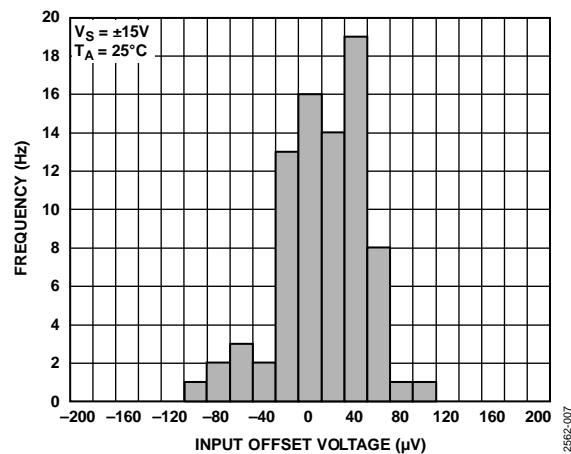


Figure 4. Input Offset Voltage Distribution, $V_S = \pm 15\text{ V}$

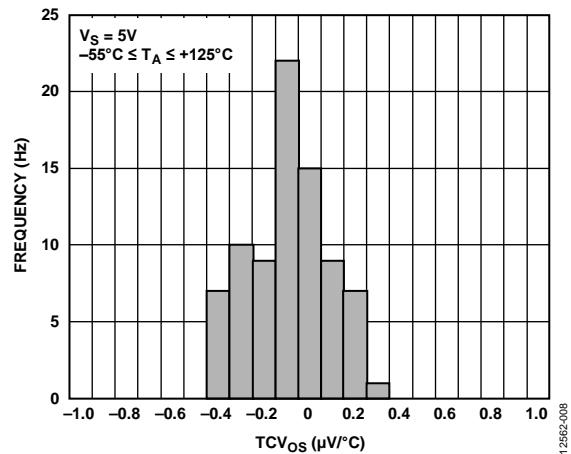


Figure 5. Input Offset Voltage Drift Distribution, $V_S = 5\text{ V}$

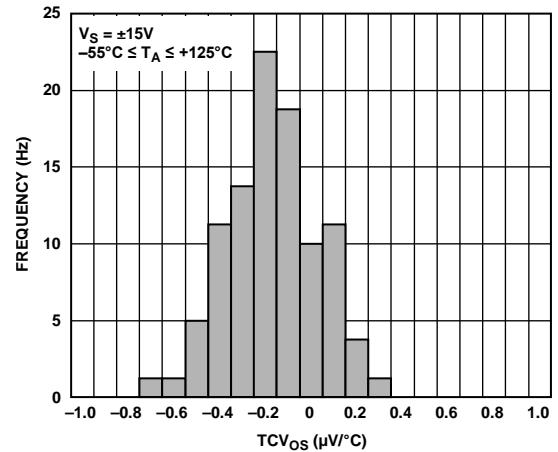


Figure 6. Input Offset Voltage Drift Distribution, $V_S = \pm 15\text{ V}$

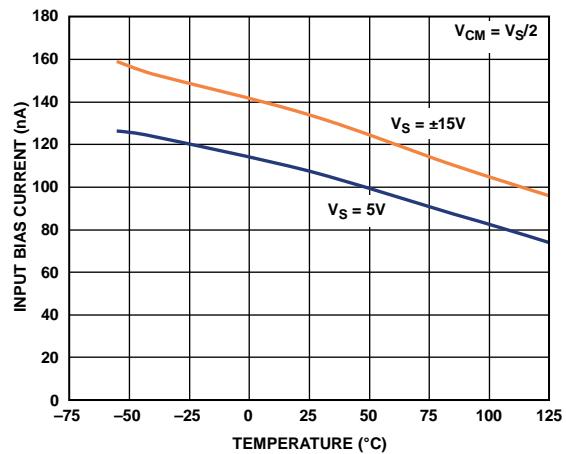


Figure 7. Bias Current vs. Temperature

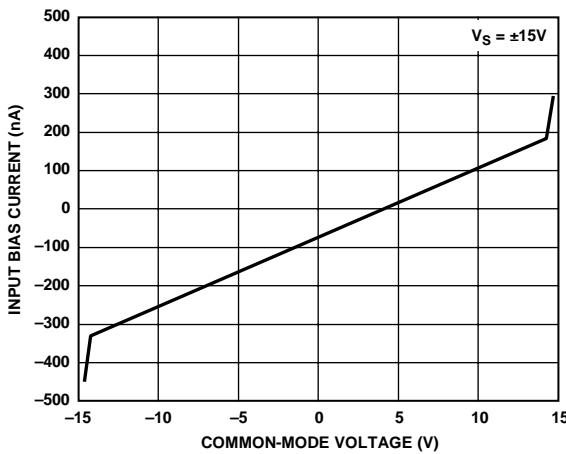
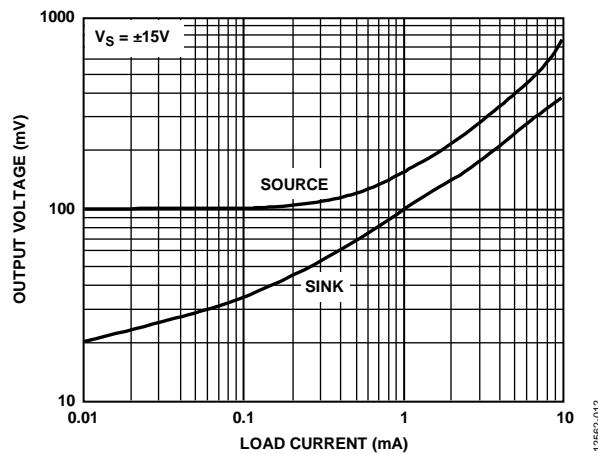
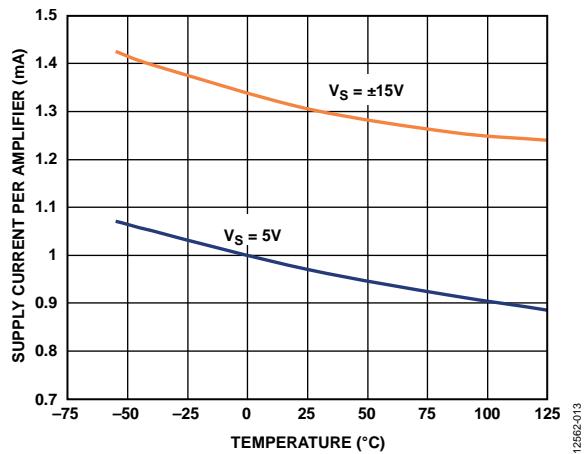


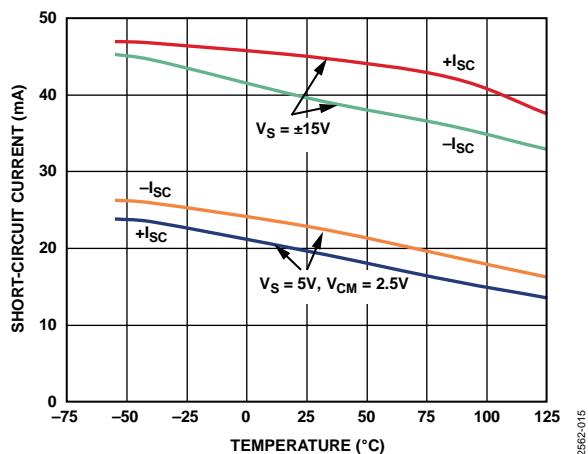
Figure 8. Input Bias Current vs. Common-Mode Voltage



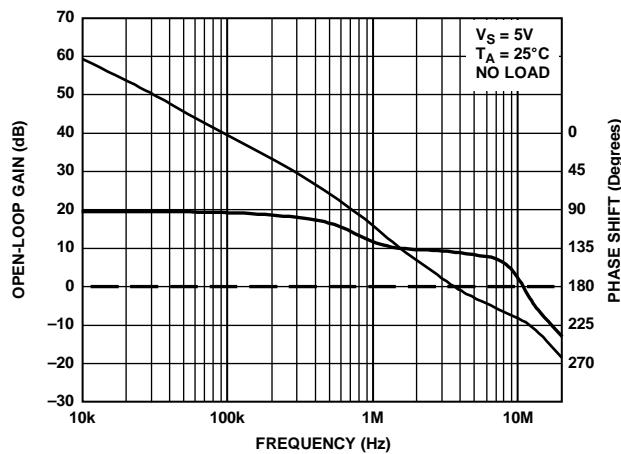
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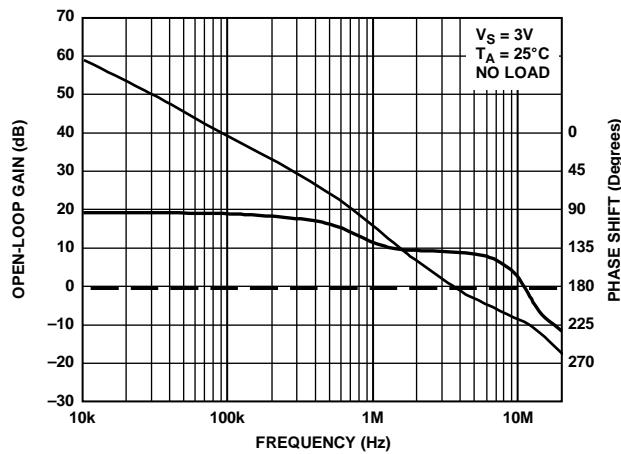
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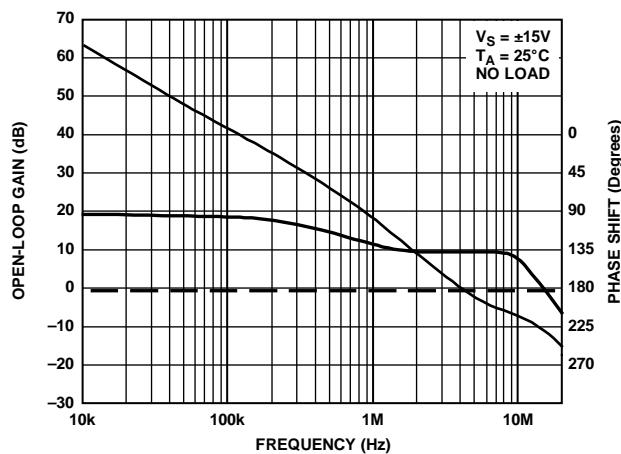
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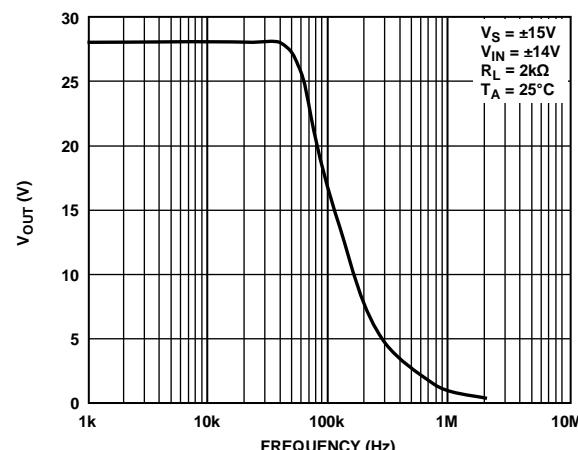
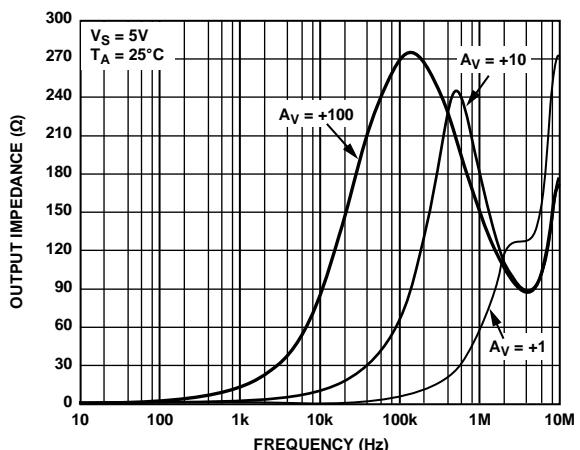
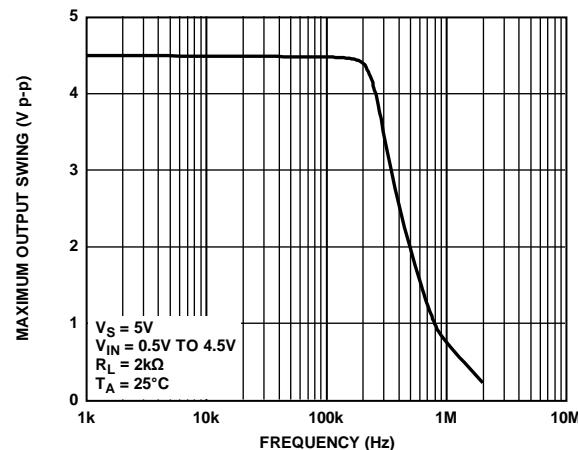
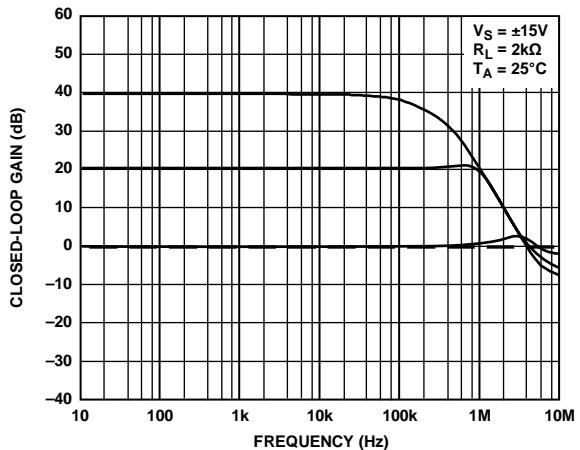
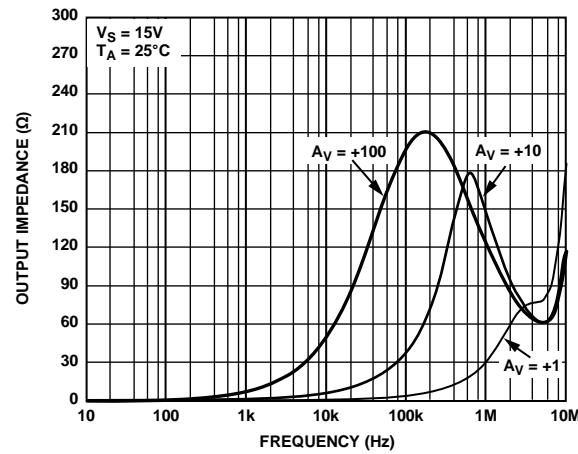
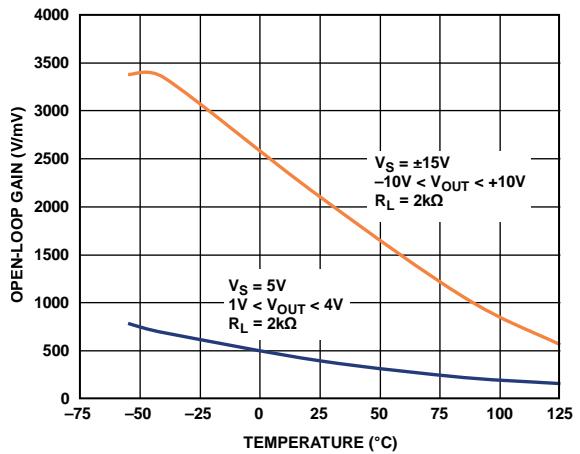
12562-016



12562-017



12562-018



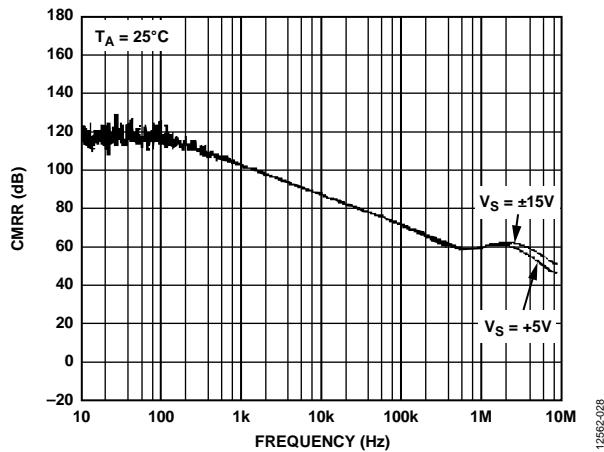


Figure 21. CMRR vs. Frequency

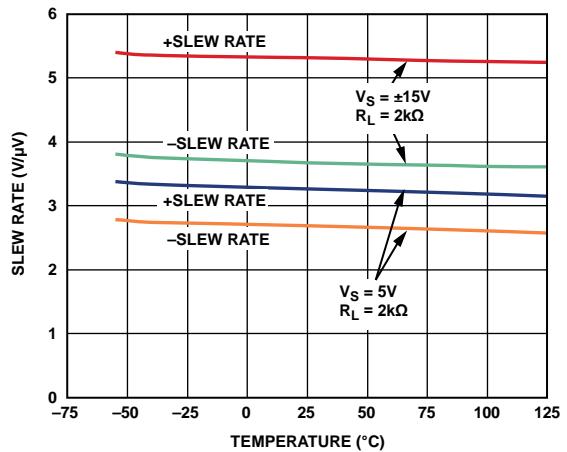


Figure 24. Slew Rate vs. Temperature

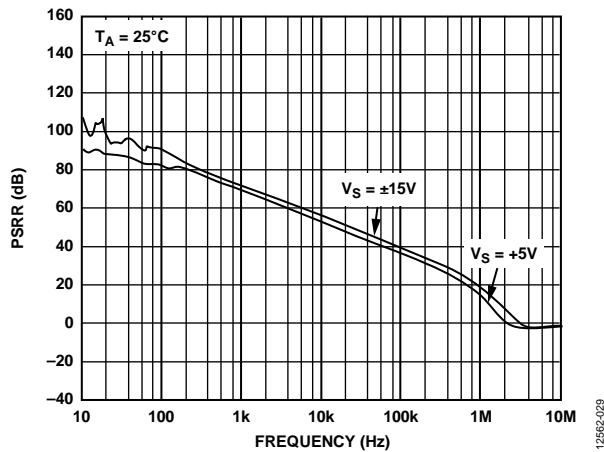


Figure 22. PSRR vs. Frequency

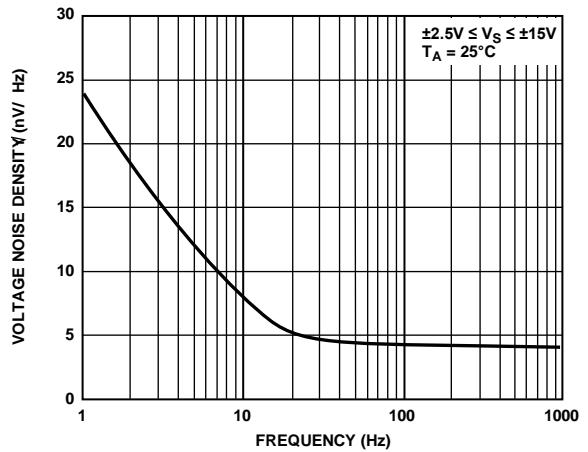


Figure 25. Voltage Noise Density vs. Frequency

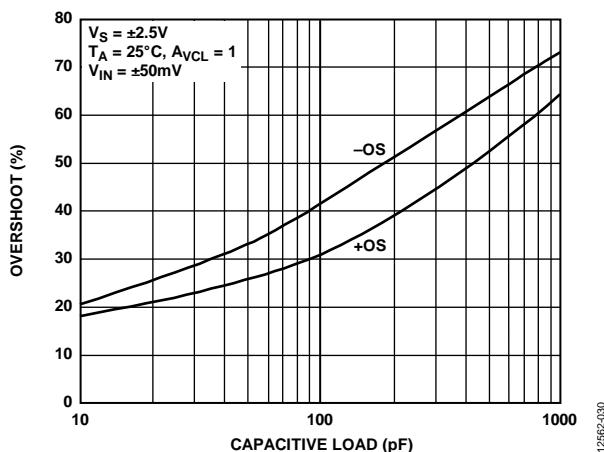


Figure 23. Small Signal Overshoot vs. Capacitive Load

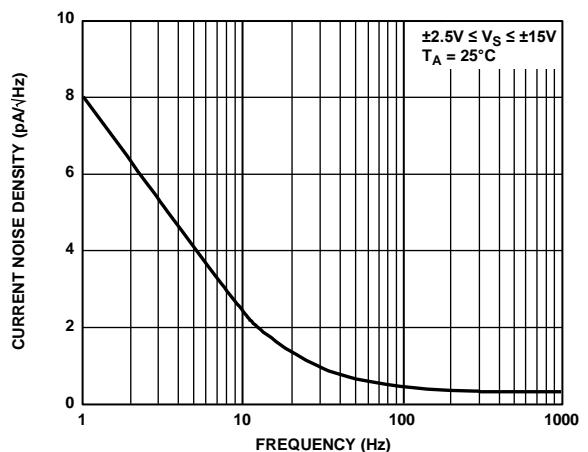


Figure 26. Current Noise Density vs. Frequency

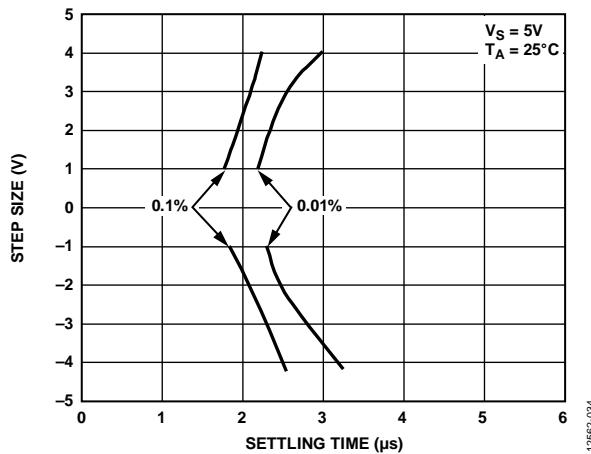
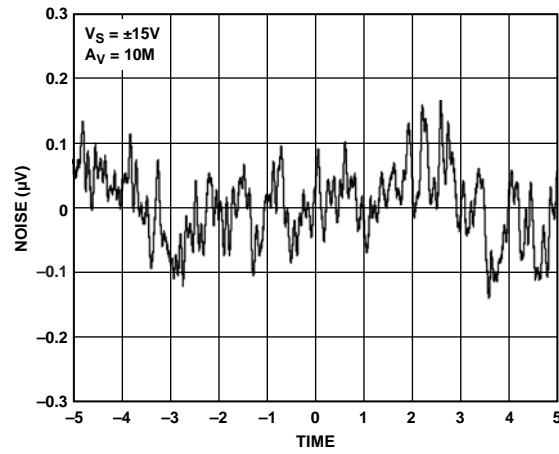
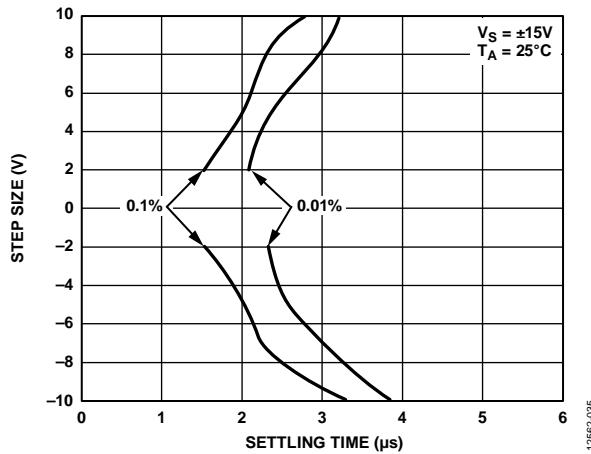
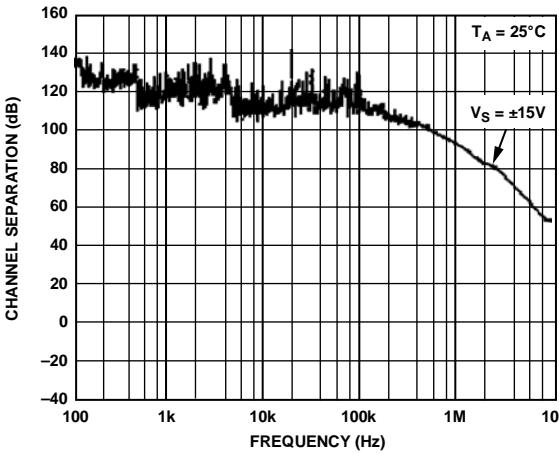
Figure 27. Step Size vs. Settling Time, $V_S = 5 V$ Figure 30. 0.1 Hz to 10 Hz Noise, $V_S = \pm 15 V$ Figure 28. Step Size vs. Settling Time, $V_S = \pm 15 V$ 

Figure 31. Channel Separation vs. Frequency

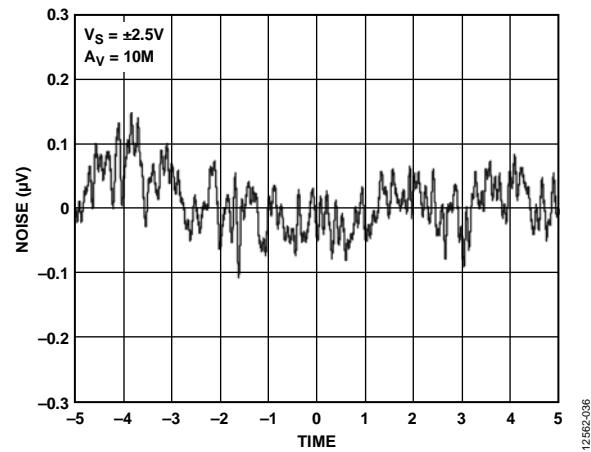
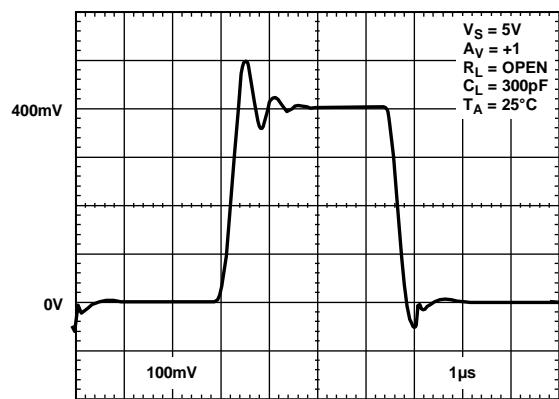
Figure 29. 0.1 Hz to 10 Hz Noise, $V_S = \pm 2.5 V$ 

Figure 32. Small Signal Transient Response

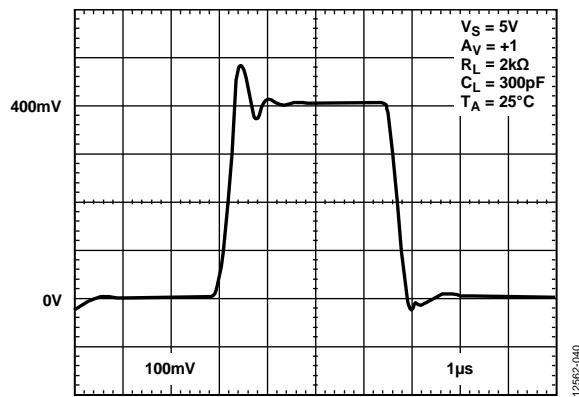


Figure 33. Small Signal Transient Response

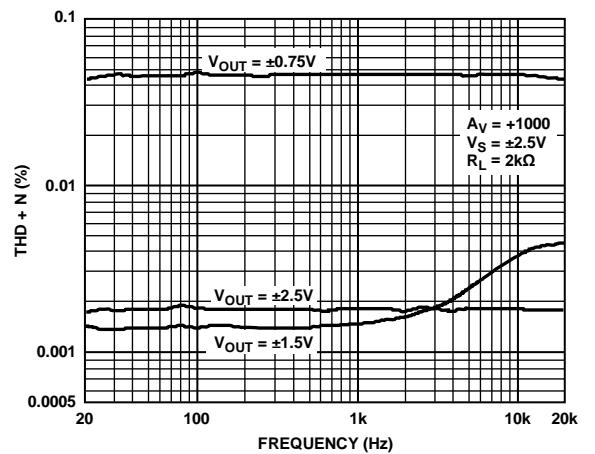
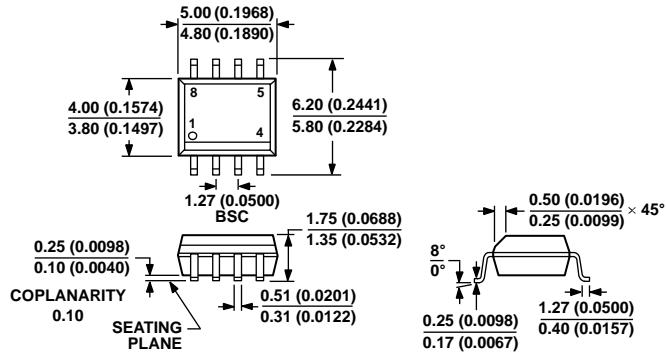


Figure 34. Total Harmonic Distortion + Noise vs. Frequency

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MS-012-AA
 CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS
 (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR
 REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

01207-A

Figure 35. 8-Lead Standard Small Outline Package [SOIC_N]

Narrow Body

(R-8)

Dimensions shown in millimeters and (inches)

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option
OP284TRZ-EP-R7	–55°C to +125°C	8-Lead Standard Small Outline Package [SOIC_N]	R-8

¹ Z = RoHS Compliant Part.

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